

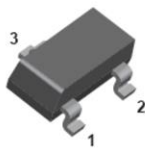
FEATURES

- Low saturation.
- Complementary To FMMT591.
- Excellent H_{FE} Linearity.

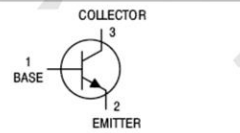
APPLICATIONS

- Switching application.

Package and Pin Configuration



SOT-23



Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

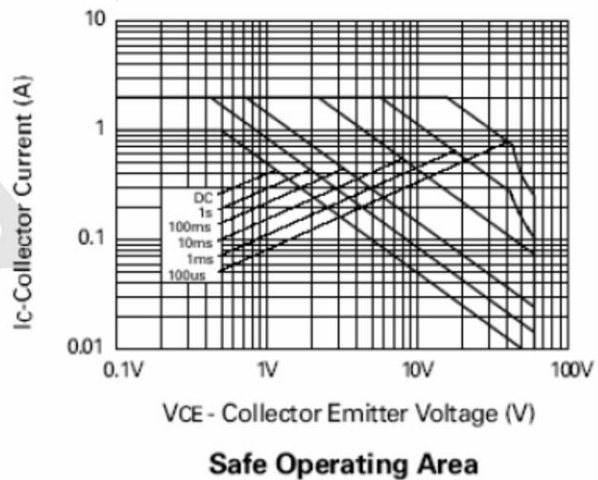
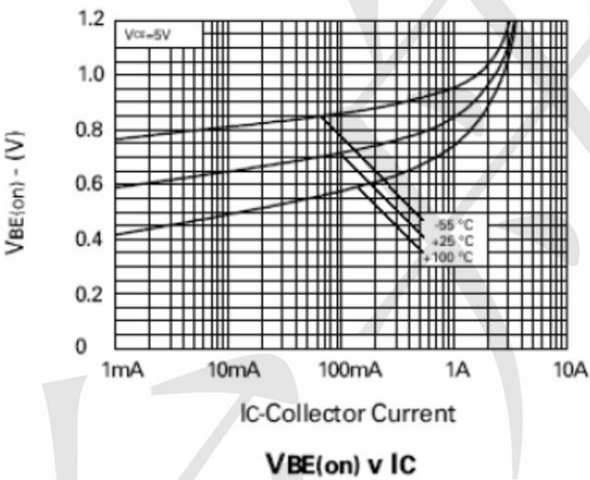
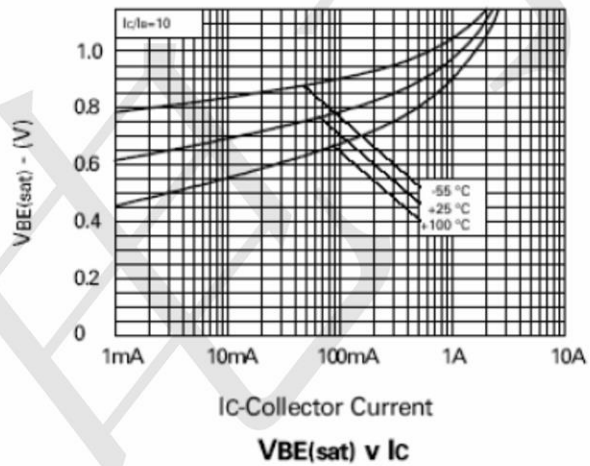
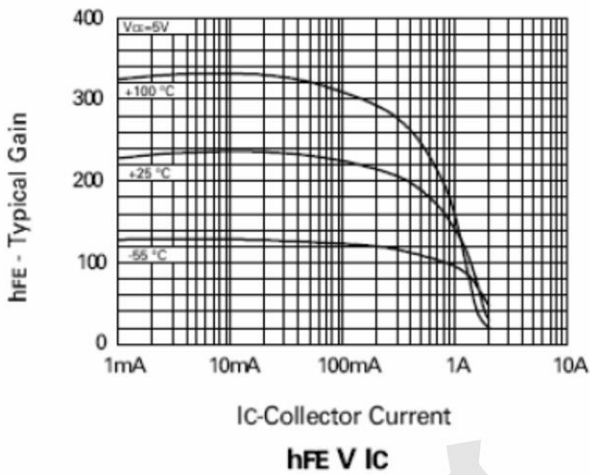
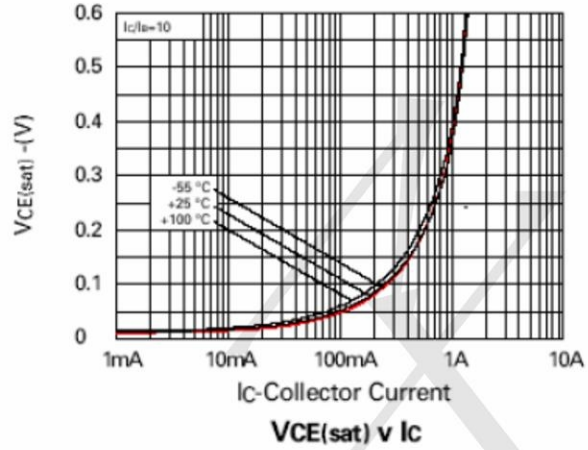
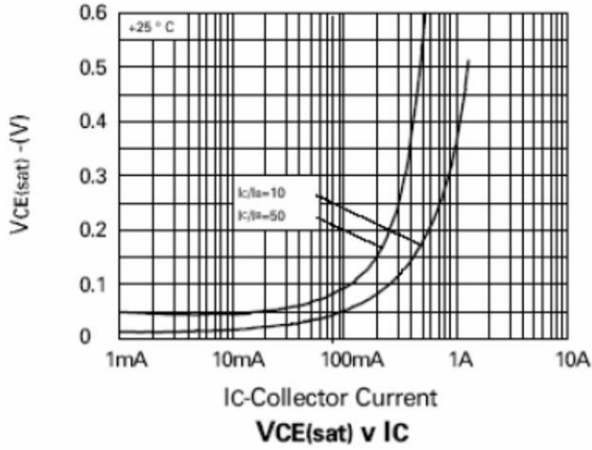
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1	A
P_C	Collector Dissipation	500	mW
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=1\text{mA}$	100			
		$V_{CE}=5\text{V}, I_C=500\text{mA}$	100		300	
		$V_{CE}=5\text{V}, I_C=1\text{A}$	80			
		$V_{CE}=5\text{V}, I_C=2\text{A}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$ $I_C=1\text{A}, I_B=100\text{mA}$			0.25 0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1\text{A}, I_B=100\text{mA}$			1.1	V
Base-emitter voltage	$V_{BE(on)}$	$I_C=1\text{A}, V_{CE}=5\text{V}$			1.0	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}$ $f=100\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$			10	pF



Typical Electrical and Thermal Characteristics





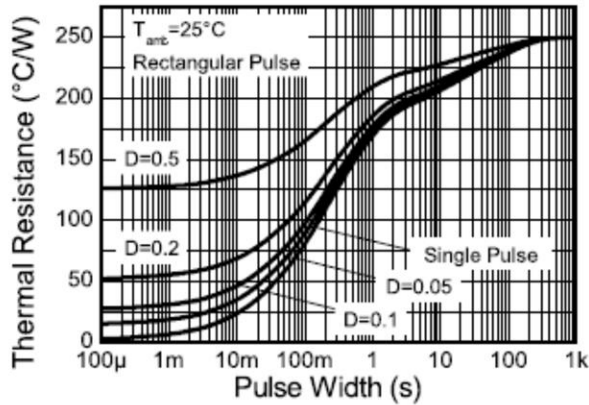
TECH PUBLIC

台舟电子

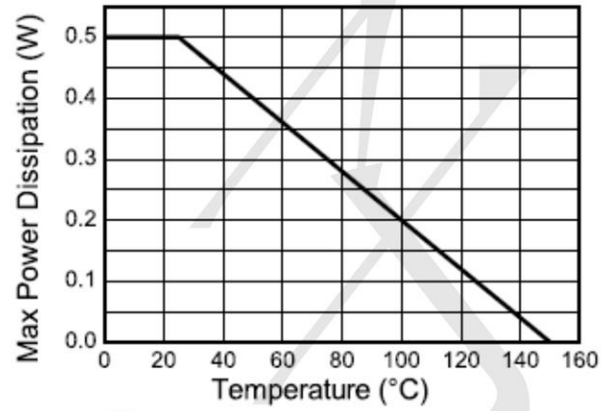
FMMT491

NPN Silicon Epitaxial Planar Transistor

www.sot23.com.tw

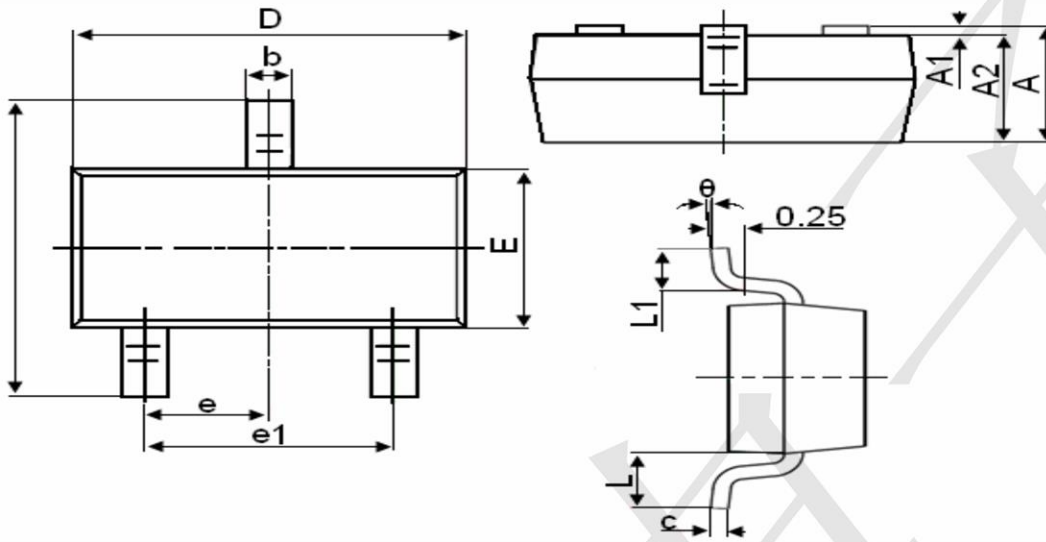


Transient Thermal Impedance



Derating Curve

Package Outline Dimensions (SOT-23)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [TECH PUBLIC](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [NTNS3A92PZT5G](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#)
[AOD464](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#)
[IPS70R2K0CEAKMA1](#) [BSF024N03LT3 G](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#)
[EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMC2700UDMQ-7](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#)
[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [IRF40H233XTMA1](#) [IPSA70R950CEAKMA1](#) [IPSA70R2K0CEAKMA1](#) [STU5N65M6](#)
[C3M0021120D](#)